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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

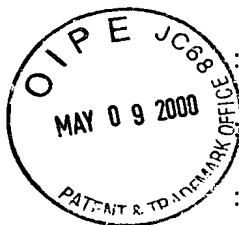
IN RE APPLICATION OF:

HISAKO AOYAMA ET AL

SERIAL NO: 09/558,053

FILED: APRIL 26, 2000

FOR: SEMICONDUCTOR DEVICE AND  
PROCESS OF FABRICATING THE  
SAME



ATTN: APPLICATION DIVISION

SUPPLEMENTAL PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Prior to examination on the merits, and supplemental to the preliminary amendment  
filed April 26, 2000, please amend the above-identified application as follows:

IN THE CLAIMS

Please add new claims 29-39 as follows:

a part of

--29. The process according to claim 28, further comprising the step of removing that  
portion of the second insulating film which is exposed to the groove, and a part of the first  
insulating film under the portion of the second insulating film, and thus forming a contact  
hole reaching to the semiconductor substrate, wherein the contact hole is buried with a metal  
in the step of forming a metal wiring in said groove.

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